



1310nm DFB Laser Diode TO-can with Aspherical Lens

Part No. C13D-5A-C2G

Features

- 1310nm InGaAsP/InP MQW-DFB laser diode (LD)
- Uncooled
- Low threshold current
- Hermetically sealed
- -40 to 85°C operating temperature
- High performance, high speed InGaAs monitor PIN photodiode (PD)
- Packaged in aspherical lens TO-56 type



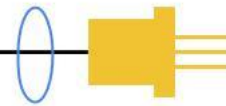
Applications

- SONET OC-12/OC-48
- SDH STM-4/STM-16
- Gigabit Ethernet
- Stable emitting source

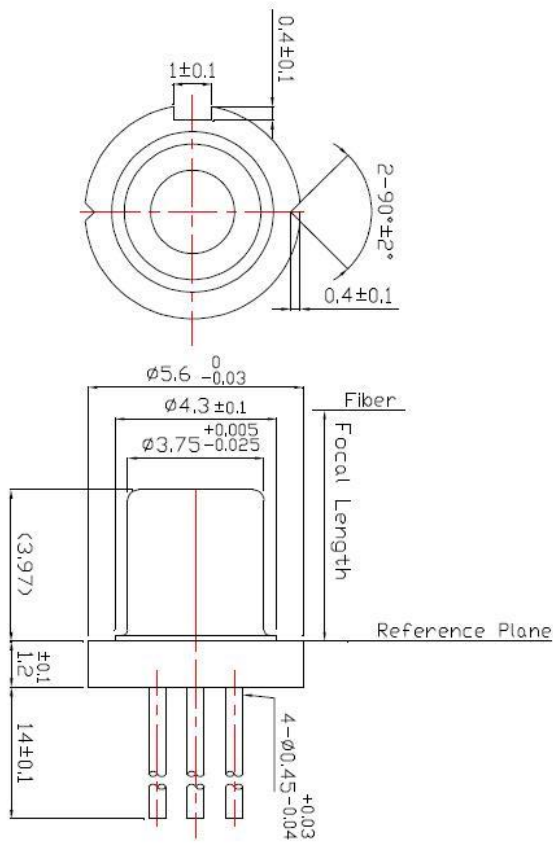
Specifications

Absolute Maximum Ratings				
Parameters	Symbol	Value	Unit	Conditions
Storage temperature	Tstg	-40~+95	°C	
Operating case temperature	Top	-40~+85	°C	
Peak optical output power	Po	15	mW	
Forward current (LD)	I _{FLD}	120	mA	
Reverse voltage (LD)	V _{RLD}	2	V	
Reverse current (PD)	I _{RPD}	2	mA	
Reverse voltage (PD)	V _{RPD}	15	V	
Soldering temperature	Stemp	260	°C	10 seconds

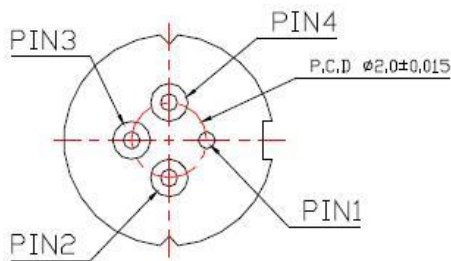
Electro-Optical Characteristics (CW @ T _c = 25°C unless otherwise noted)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold current	I _{th}	—	10	15	mA	CW
Operating voltage	V _{op}	—	—	1.4	V	CW, Pop=5mW
Operating current	I _{op}	—	—	35	mA	Pop=5mW
Slope efficiency	η	0.25	—	—	mW/mA	CW, Pop=5mW
Peak wavelength	λ _p	1290	1310	1330	nm	CW, Pop
Side-mode suppression rate	SMSR	35	—	—	nm	CW, Pop, T _c =-20~85°C
Fiber Coupling Power	P _f	1.5	—	—	mW	CW, P _o =5mW, SMF (10/125)
Focal Length	D _f	7.0	7.5	8.0	mm	CW, P _o =5mW, SMF (10/125)
Rise time	T _r	—	80	120	ps	I _b =I _{th} , 20%~80%
Fall time	T _f	—	100	150	ps	I _b =I _{th} , 20%~80%
Monitor current	I _m	80	—	1000	uA	Pop, V _{rp} =5V
Monitor dark current	I _d	—	—	100	nA	V _{rp} = 5V
Monitor capacitance	C	—	—	15	pF	V _{rp} = 5V, f=1MHZ



Outline Dimensions (unit: mm)



Pin Assignment



Pin Number	Function
1	Case
2	LD Cathode
3	PD Anode
4	LD Anode, PD Cathode

Note: Specifications are subject to change without notice.